"Yت / Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

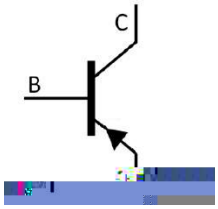
◕È / Features

Low current, high voltage.

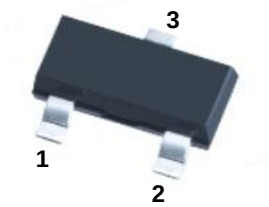
¥ ِ / Applications

Telephony and professional communication equipment.

Л ُ ً ǫ ≠ ɛ / Equivalent Circuit



ã ﺍ ◌ً / Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

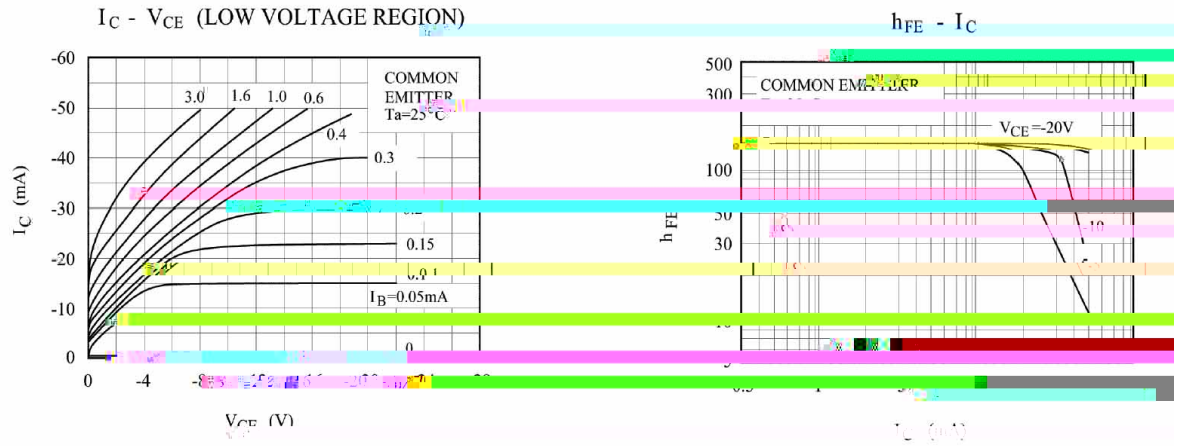
ǫ ˂ z ł . ʜ ↄ / h_{FE} Classifications & Marking

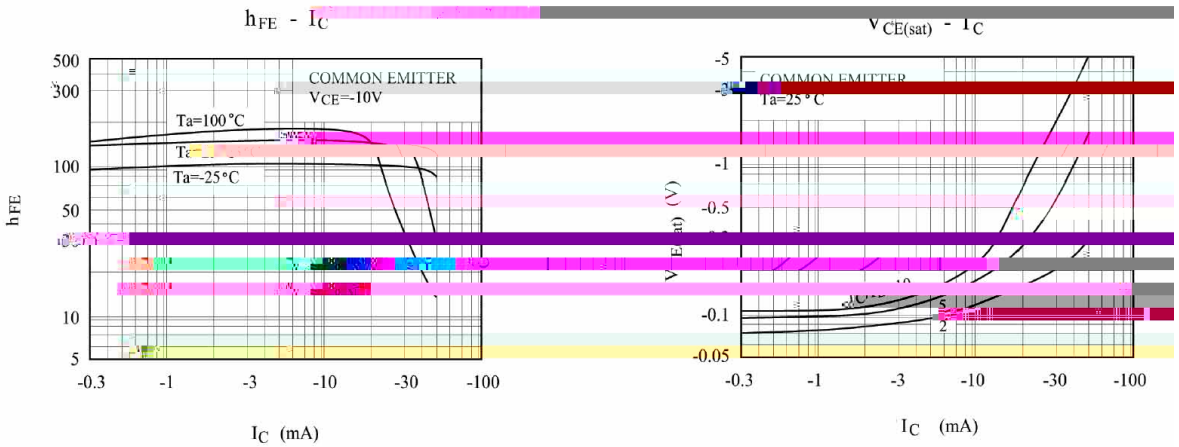
h_{FE} Range	>50
Marking	H1W

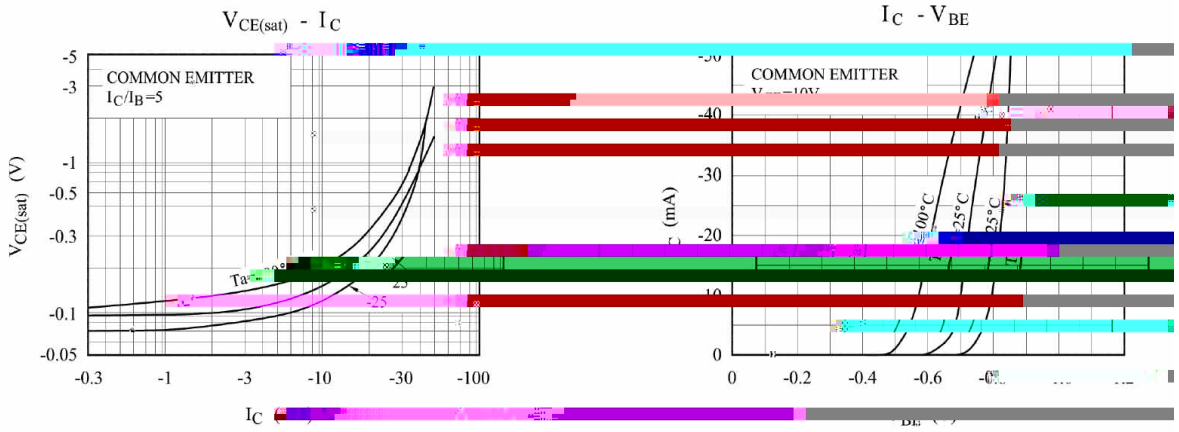
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-50	mA
Peak Collector Current - Continuous	I_{CM}	-100	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA I_E=0	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-300			V
Emitter to Base Breakdow V						

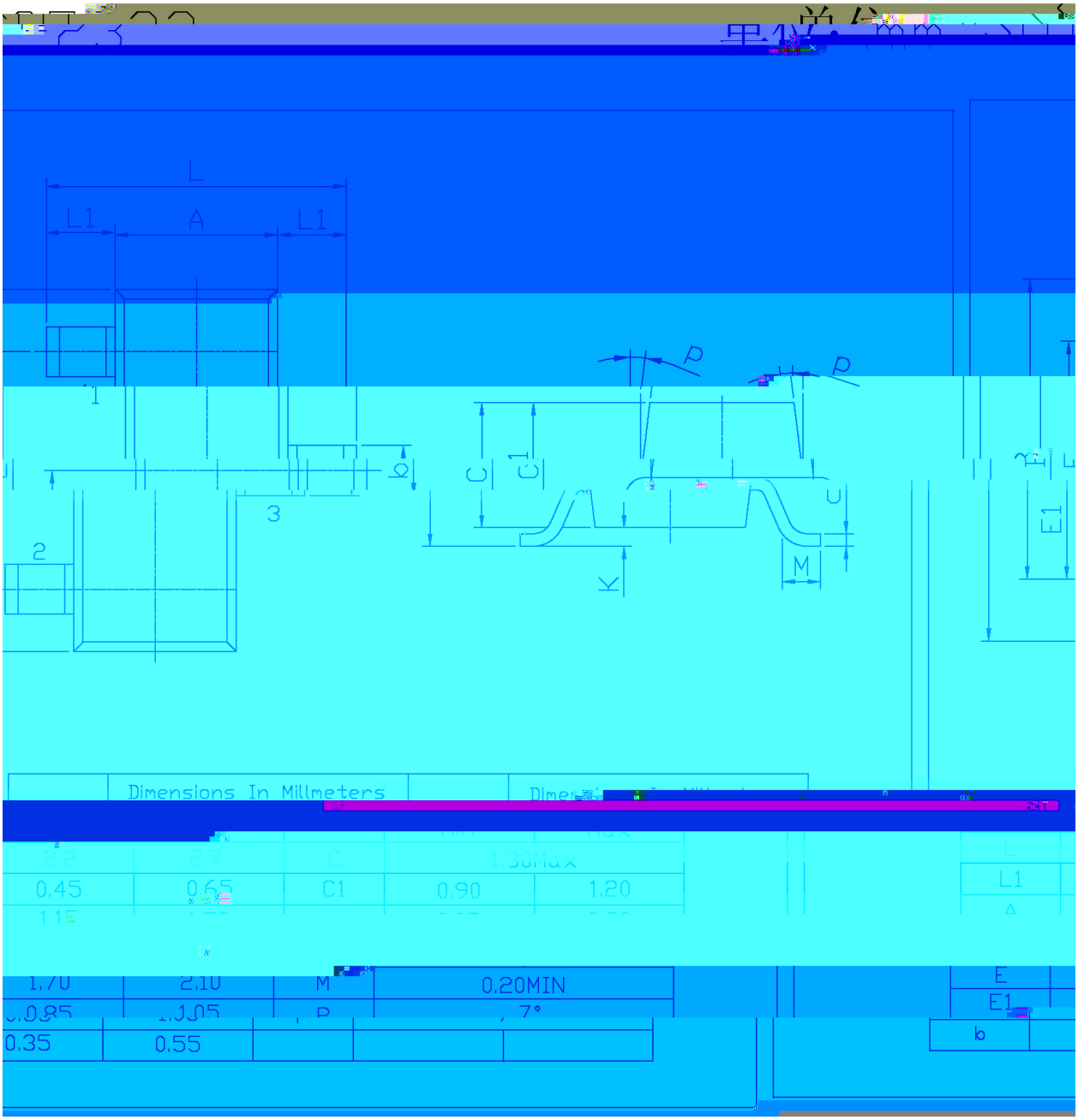
≠ Ǝ ̃Ạ´E ∀ ƒ / Electrical Characteristic Curve



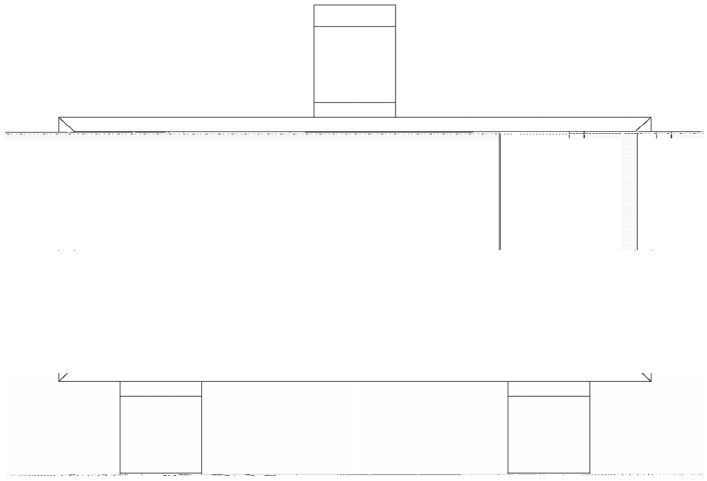




ᵘ Ė Ò Ļ ʃ / Package Dimensions



Ł. Ł Ω / Marking Instructions



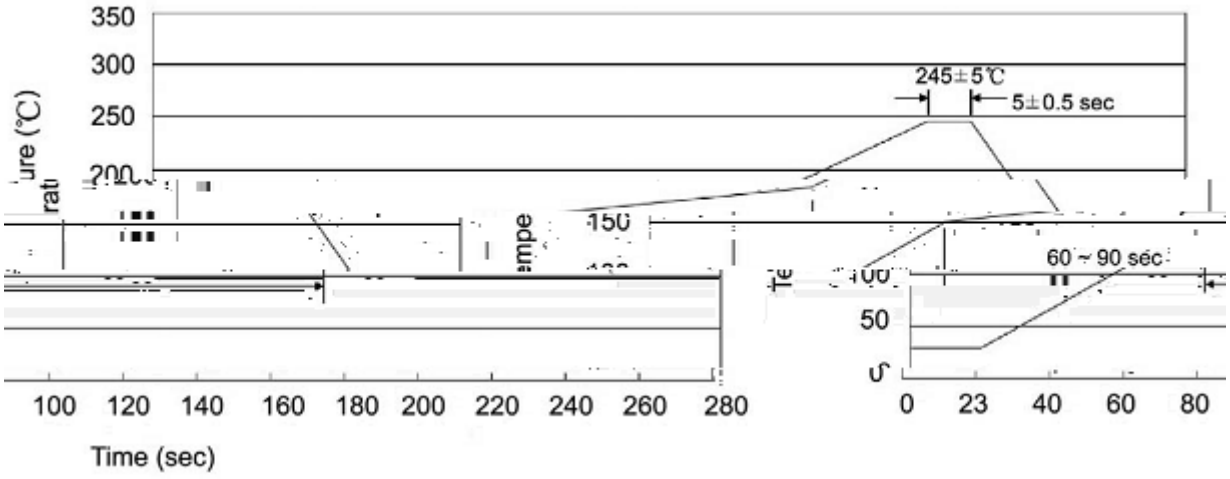
H

1W

Note:

H: Company Code.

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Note:

1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	245±5			5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

ⅎ ü q ‾ `Y Ţ / Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

ɒ Ŀ ≮ — / Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

ä ⅴ ŗ Ω / Notices